

Computational Materials Design (CMD<sup>®</sup>) Workshop

Spintronic Design Course

## Spintronic · Design · Magnetic control II

Materials Design based on band structures

**Kohji Nakamura**  
Mie University

Outline

- Introduction
- Electronic structures and magnetism in transition-metals
- Electronic structures and magnetism at surfaces/thin films
- Control of magnetism by tuning atomic-layer alignments
- Control of magnetism by external electric field
- Summary

### Role of materials in spintronics

**Magnetic thin films**

**Artificial multilayer thin-films**

**Spin-related properties**

- Magnetization
- Perpendicular MA
- Magnetic (tunnel) resistivity
- Spin (Hall) current
- Spin Seebeck/Peltier effect
- Spin (orbital) torque
- ...

**Required high-performance**

**Spintronic devices**

- HDD
- MRAM
- Magnetic domain memory
- Spin microwave/mill-meter wave oscillator
- Spin diode/transistor
- ...

Magnetic field

Electric field

Heat

Light

Pressure

Current

External-field response

### An example of spintronic development

**1857**

Discovery of Magneto-resistivity

**1988(1995)**

Giant/Tunneling Magneto-resistivity

**2006**

MRAM(4Mb) Products

**2007**

In-plane MA      Out-of-plane MA (PMA)

**2010**

By current (spin injection)

**2009**

Fe/MgO Interfacial PMA

**Key technology**

**Magnetization direction**

**Magnetization switching**

By Magnetic field

By current (spin injection)

*E-field effect*

### Role of first principles calculations in materials design

- Quantum mechanics !
- No use of empirical parameters !
- High accuracy in computations !

- Interpretation of experiments
- Understanding
- Prediction with **no restriction of materials**

**Unresolved issues**

Strong correlated systems, Exited states, etc.

sp-electron systems: H, He, Li, Be, B, C, N, O, F, Ne, Na, Mg, Al, Si, P, S, Cl, Ar, K, Ca, Sc, Ti, V, Cr, Mn, Fe, Co, Ni, Cu, Zn, Ga, Ge, As, Se, Br, Kr, Rb, Sr, Y, Zr, Nb, Mo, Tc, Ru, Rh, Pd, Ag, Cd, In, Sn, Sb, Te, I, Xe, Cs, Ba, La, Hf, Ta, W, Re, Os, Ir, Pt, Au, Hg, Tl, Pb, Bi, Po, At, Rn, Fr, Ra, Ac

d-electron systems: K, Ca, Sc, Ti, V, Cr, Mn, Fe, Co, Ni, Cu, Zn, Ga, Ge, As, Se, Br, Kr, Rb, Sr, Y, Zr, Nb, Mo, Tc, Ru, Rh, Pd, Ag, Cd, In, Sn, Sb, Te, I, Xe, Cs, Ba, La, Hf, Ta, W, Re, Os, Ir, Pt, Au, Hg, Tl, Pb, Bi, Po, At, Rn, Fr, Ra, Ac

f-electron systems: Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu, Th, Pa, U, Np, Pu, Am, Cm, Bk, Cf, Es, Fm, Md, No, Lr

Goal: Prediction of material properties from the periodic table

### First principles calculations

**① Kohn-Sham equation**

$$[-\nabla^2 + V_c(\mathbf{r}) + V_{\text{eff}}(\mathbf{r})]\psi_i(\mathbf{r}) = \epsilon_i \psi_i(\mathbf{r})$$

$E_{\text{xc}}^{\text{LDA}}[n] \approx \int n(\mathbf{r}) \epsilon_{\text{xc}}^{\text{LDA}}(n(\mathbf{r}))$

**exchange correlation potential**

**Coulomb potential**    **wave function (basis)**

**② Total energy**

$$E_{\text{total}} = \sum_{i=1, \epsilon_i < E_F}^N \epsilon_i$$

**Kohn-Sham eigenvalues (band structure, density of states)**

$$-\frac{1}{2} \left[ \int V_c(\mathbf{r}) n(\mathbf{r}) d\mathbf{r} + \sum_{\sigma} \int [v_{\sigma}^{\text{xc}}(\mathbf{r}) - \epsilon_{\sigma}^{\text{xc}}(\mathbf{r})] n_{\sigma}(\mathbf{r}) d\mathbf{r} \right] - \frac{1}{2} \sum_{\mu} Z_{\mu} V_{C,\mu}(\mathbf{R}_{\mu})$$

**double counting term**

- Introduction
- Electronic structures and magnetism in transition-metals
- Electronic structures and magnetism at surfaces/thin films
- Control of magnetism by tuning atomic-layer alignments
- Control of magnetism by external electric field
- Summary

### Eigenvalues and eigenstates of electron orbitals in atoms

$$\psi_{nlm}(\mathbf{r}) \approx R_{nl}(r) Y_{lm}$$

Li :  $1s^2 2s$   
 Na :  $1s^2 2s^2 2p^6 3s$   
 K :  $1s^2 2s^2 2p^6 3s^2 3p^6 4s$

**Atomic core**

**① Orthogonalization in orbitals**  
 $\langle \psi_j | \psi_i \rangle = 0$

**② Spatial spread of wave function Hybridization in crystals**

**FIGURE 1-2**  
 The three s states of lowest energy for atomic hydrogen. The orbitals, multiplied by r, are plotted as a function of distance from the nucleus.

### Hybridization: bonding and anti-bonding orbitals

Atomic orbitals  $\phi_1$  and  $\phi_2$  combine to form:

**Antibonding state**  $\psi_a = \frac{1}{\sqrt{2}}(\phi_1 - \phi_2)$

**Bonding state**  $\psi_b = \frac{1}{\sqrt{2}}(\phi_1 + \phi_2)$

**Homo bonds**    **Polar bonds**

**Antibonding**    **Antibonding**

**Bonding**    **Bonding**

$V_2 = \langle \phi_2 | V | \phi_1 \rangle$

### Occupation of electrons

Number of electrons

1      2      3      4

$H_2^+$      $H_2$      $He_2^+$      $He_2$

stable                    unstable

### Electrons in crystal

**Free-electron-like**

$$\left(-\frac{\nabla^2}{2} + V_0\right)\psi = \epsilon\psi \quad \epsilon \propto \frac{k^2}{2}$$

↓

**atomic-like**

$$\left(-\frac{\nabla^2}{2} + V_{atom}(r)\right)\psi_c = \epsilon\psi_c \quad \epsilon = \epsilon_{nl}$$

↓

**Bloch function**

$$\psi_k(\mathbf{r}) = e^{i\mathbf{k}\cdot\mathbf{r}} u_k(\mathbf{r})$$

$$u_k(\mathbf{r} + \mathbf{R}_j) = u_k(\mathbf{r})$$

$\langle \psi_v | \psi_c \rangle = 0$

Orthogonal

### Cohesive energy and spin polarization in transition-metals

**Non-spin Polarized**

**LDA results vs. experiments**

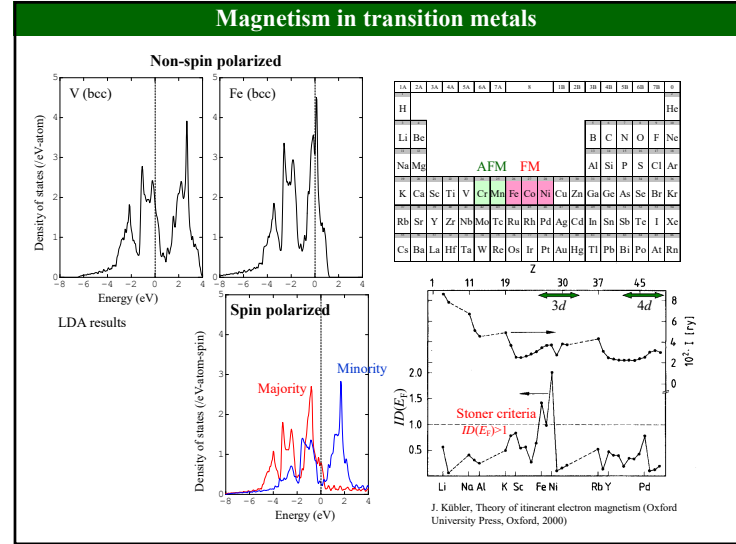
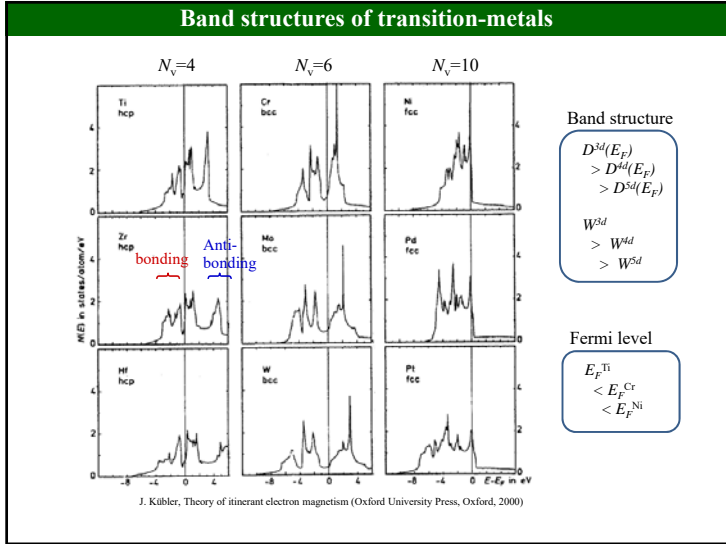
V. L. Moruzzi, J.F. Janak, A.R. Williams, Calculated electronic properties of metals (Pergamon Press, New York, 1978)

### Magnetism

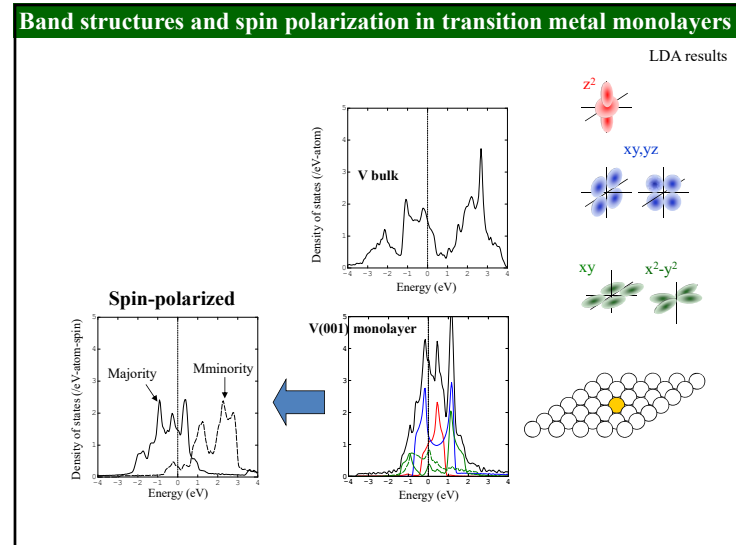
**Question:**  
Why do ferromagnetism appear only in Fe, Co and Ni?

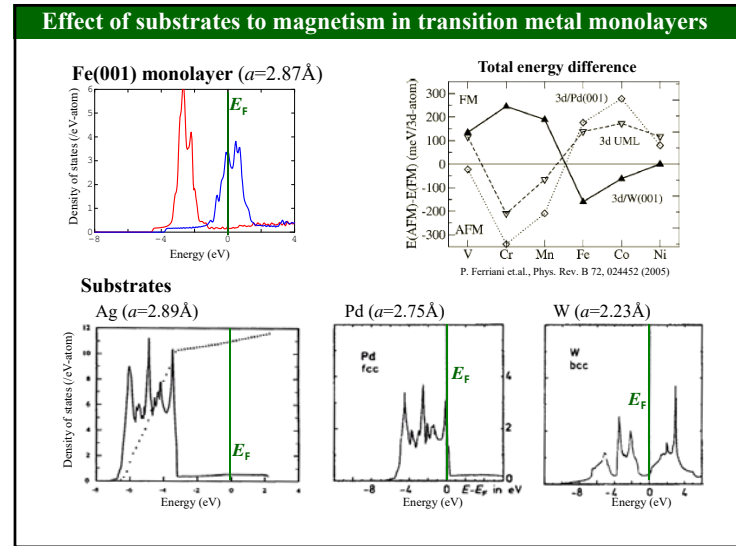
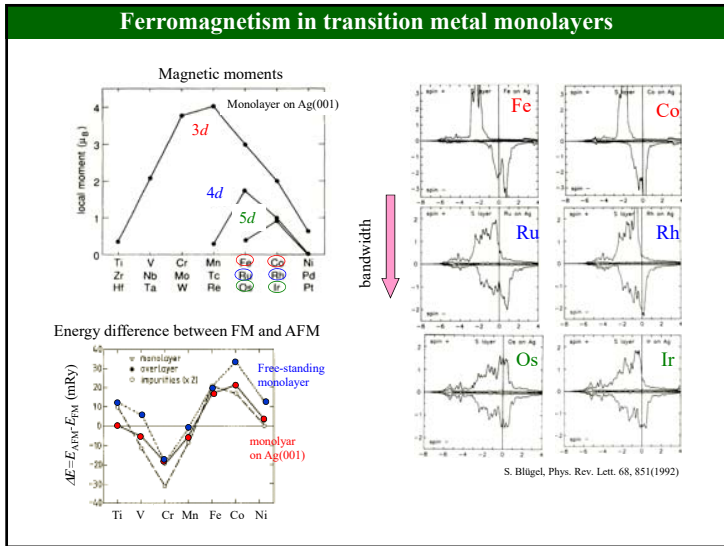
1A	2A	3A	4A	5A	6A	7A	8	1B	2B	3B	4B	5B	6B	7B	0		
H															He		
Li	Be									B	C	N	O	F	Ne		
Na	Mg									Al	Si	P	S	Cl	Ar		
K	Ca	Sc	Ti	V	Cr	Mn	Fe	Co	Ni	Cu	Zn	Ga	Ge	As	Se	Br	Kr
Rb	Sr	Y	Zr	Nb	Mo	Tc	Ru	Rh	Pd	Ag	Cd	In	Sn	Sb	Te	I	Xe
Cs	Ba	La	Hf	Ta	W	Re	Os	Ir	Pt	Au	Hg	Tl	Pb	Bi	Po	At	Rn

	Magnetic order	Transition Temperature(K)	Crystal structure	Number of valence
Fe	Ferromagnetic	1043	bcc	8
Co	Ferromagnetic	1388	hcp	9
Ni	Ferromagnetic	627	fcc	10



- Introduction
- Electronic structures and magnetism in transition-metals
- **Electronic structures and magnetism at surfaces/thin films**
- Control of magnetism by tuning atomic-layer alignments
- Control of magnetism by external electric field
- Summary





- Introduction
- Electronic structures and magnetism in transition-metals
- Electronic structures and magnetism at surfaces/thin films  
Magnetocrystalline anisotropy (MCA)
- Control of magnetism by tuning atomic-layer alignments
- Control of magnetism by external electric field
- Summary

### Magnetocrystalline anisotropy (MCA)

**MTJ device** ✓Non-volatility  
✓Large capacity  
✓High-speed

[1] Ferromagnetic  
Insulator  
Ferromagnetic

[1] S. Yuasa, et al., Nature Materials 3, 868 (2004).

Many Applications

- MRAM
- Magnetic sensor

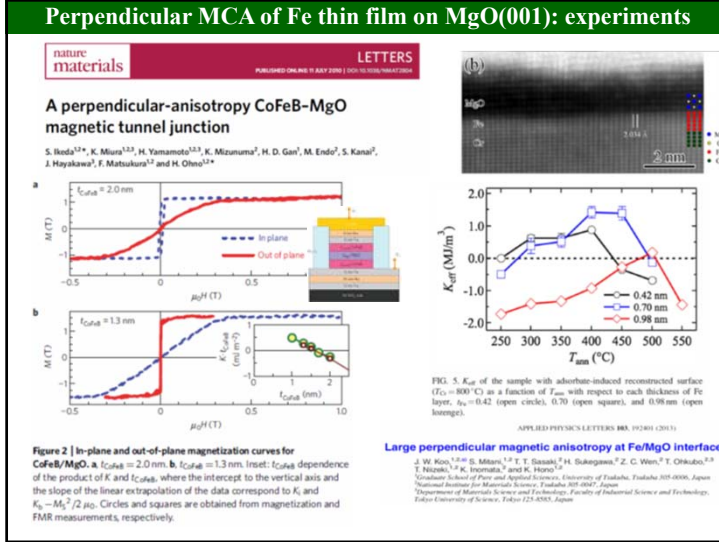
In-plane MCA

➔

Large advance  
for applications

Out-of-plane MCA

We, here, design thin films with large MCA



### First principles calculations of MCA energy

**Spin-orbit coupling**

$$H^{SOC} = \frac{1}{4c^2} \frac{1}{r} \frac{dV}{dr} \ell \cdot \sigma = \xi(r) \begin{bmatrix} \ell_z & \ell_- \\ \ell_+ & -\ell_z \end{bmatrix}$$

Admixture of spin-up and down components

SOC strength,  $\xi(r)$

~50 meV for 3d-metals

**Magneto-crystalline anisotropy energy**

$$E_{MCA} = E_{total}(\rightarrow) - E_{total}(\uparrow)$$

~0.1 meV/atom

**Force theorem**

$$\approx \{E[\rho_0, \mathbf{m}_0(\rightarrow)] - E[\rho_0, \mathbf{m}_0(\uparrow)]\}$$

$$= \sum_{\mathbf{k}} \left[ \sum_{\sigma} \epsilon_{\mathbf{k},\sigma}(\rightarrow) - \sum_{\sigma} \epsilon_{\mathbf{k},\sigma}(\uparrow) \right]$$

$E_{MCA} < 0$  : in-plane MCA

$E_{MCA} > 0$  : Perpendicular MCA

### Perturbation method of MCA energy

$$E_{MCA}(\sigma) = E^{SOC}(x) - E^{SOC}(z)$$

$$\approx \Delta E^{dd} + \Delta E^{ud}$$

$$\Delta E^{dd} = E^{dd}(x) - E^{dd}(z)$$

$$= \xi^2 \sum_{o_-} \sum_{u_-} \frac{|\langle o_- | L_z | u_- \rangle|^2 - |\langle o_- | L_x | u_- \rangle|^2}{\epsilon_{u_-} - \epsilon_{o_-}}$$

$$\Delta E^{ud} = E^{ud}(x) - E^{ud}(z)$$

$$= \frac{\xi^2}{\Delta E_{ex}} \sum_{o_-} \langle o_- | 3L_z^2 - L^2 | o_- \rangle$$

Spin-up

Spin-down

R. Wu, A.J. Freeman, J. Magn. Magn. Mater. 200, 498(1999)

### Rule in origin of MCA in $\Delta E^{dd}$

$$\Delta E^{dd} = \xi^2 \sum_{o_-} \sum_{u_-} \frac{|\langle o_- | L_z | u_- \rangle|^2 - |\langle o_- | L_x | u_- \rangle|^2}{\epsilon_{u_-} - \epsilon_{o_-}}$$

**Positive  $E_{MCA}$**

$|\langle o | L_z | u \rangle|^2$

$|\langle xz, yz | L_z | xz, yz \rangle|^2$

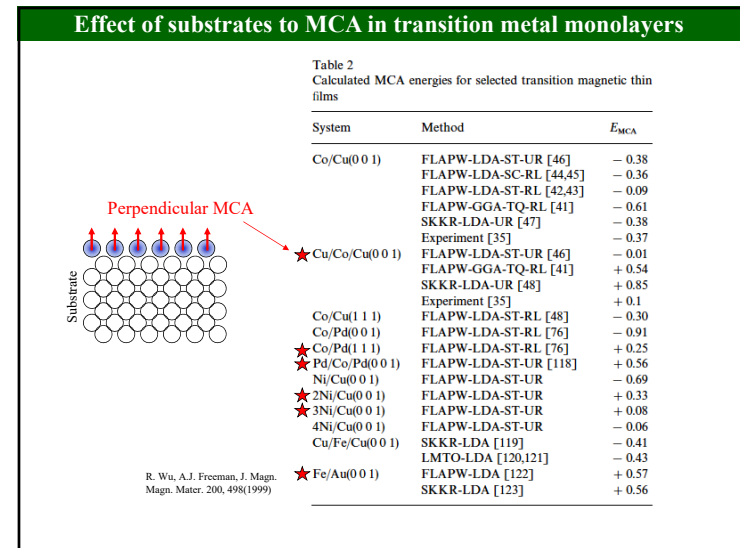
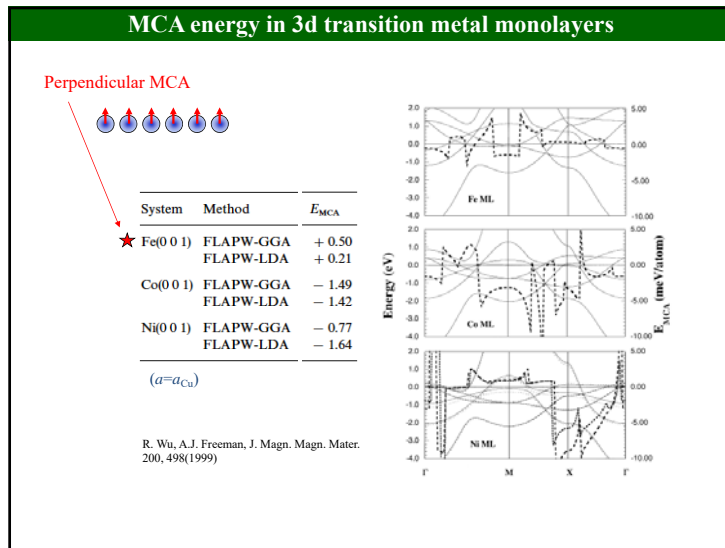
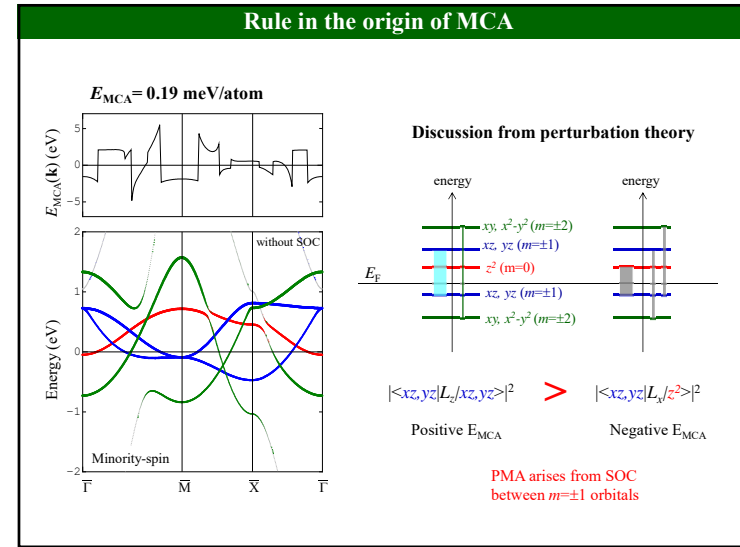
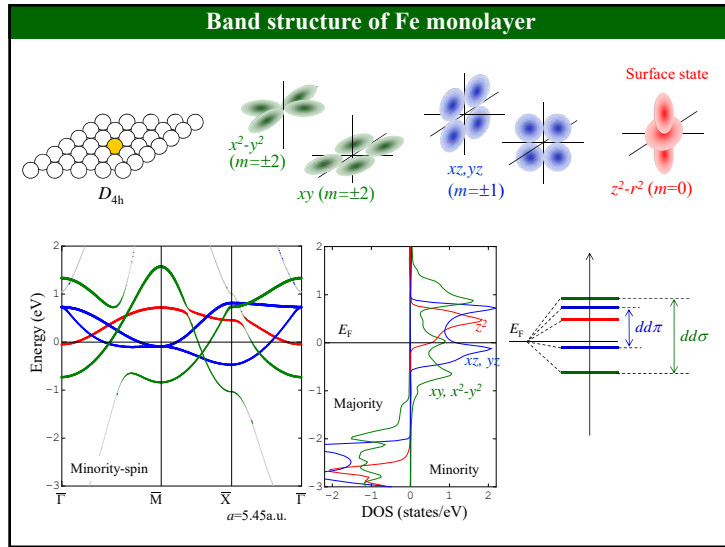
Perpendicular MCA

**Negative  $E_{MCA}$**

$|\langle o | L_x | u \rangle|^2$

$|\langle xz, yz | L_x | xz, yz \rangle|^2$

In-plane MCA




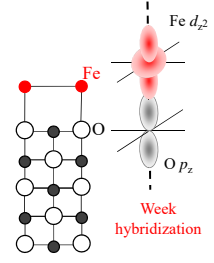
### Perpendicular MCA at Fe/MgO(001) interface: Theory

$$E_{MCA} = E^{\text{SOC}}(\rightarrow) - E^{\text{SOC}}(\uparrow)$$

	$E_{MCA}$ (meV/ $a^2$ )
Free-standing Fe monolayer	0.19
Fe/MgO	1.28
Au <sub>3</sub> /Fe <sub>3</sub> /MgO	0.94

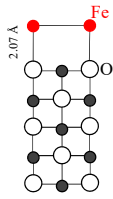
LDA  
Nakamura et al., PRB 81, 220409, (2010)





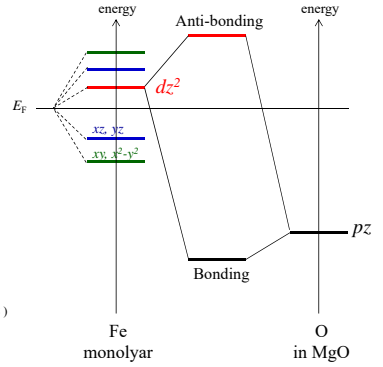
Origin of interfacial perpendicular MCA  
Fe dz<sup>2</sup> - O p<sub>z</sub> hybridization

### Fe d<sub>z<sup>2</sup></sub> - O p<sub>z</sub> hybridization at Fe/MgO interface



Fe/MgO interface structure

Urano and Kanaji, J. Phys. Soc. Jpn. 57, 3403, (1988)  
Li and Freeman, Phys. Rev. B 43, 780, (1991)  
Meyerheim et al., Phys. Rev. B 65, 144433, (2002)



energy

Anti-bonding

Bonding

Fe monolayer

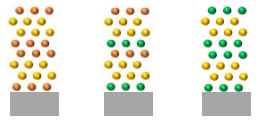
O in MgO

Shimabukuro, Physica E, 42, 1014 (2010)  
Nakamura et al., PRB 81, 220409, (2010)

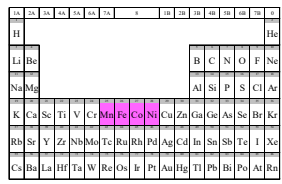
- Introduction
- Electronic structures and magnetism in transition-metals
- Electronic structures and magnetism at surfaces/thin films
- Control of magnetism by tuning atomic-layer alignments
- Control of magnetism by external electric field
- Summary

### Control of MCA by tuning atomic-layer alignments

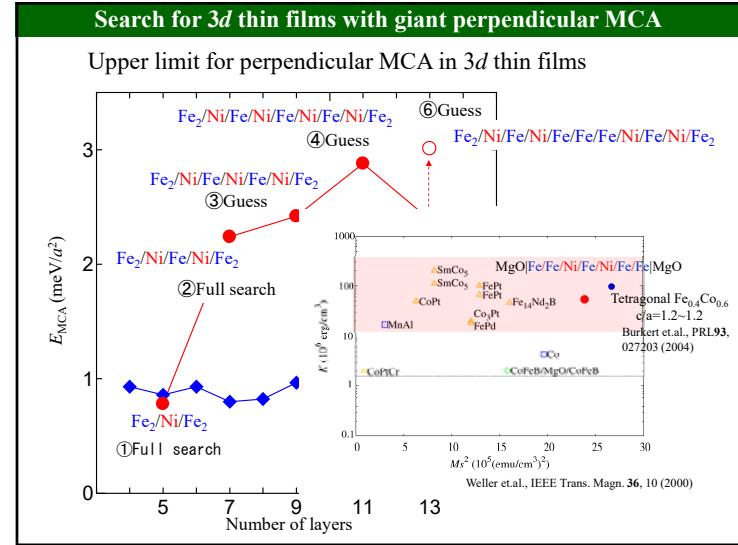
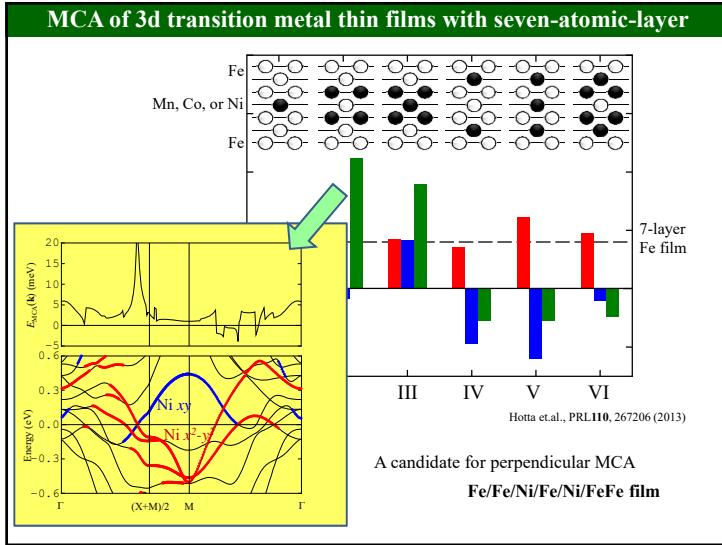
Interfaces, superlattices, multilayers



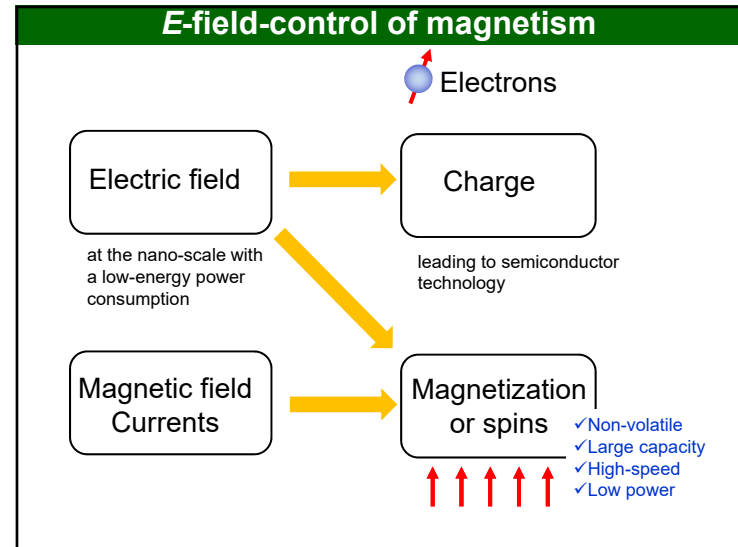
Thin films with large perpendicular MCA, consisting of only 3d metals

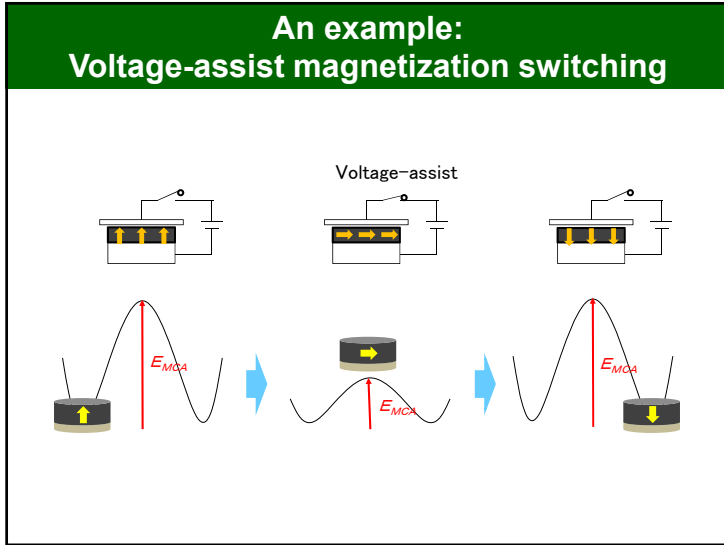






- Introduction
- Electronic structures and magnetism in transition-metals
- Electronic structures and magnetism at surfaces/thin films
- Control of magnetism by tuning atomic-layer alignments
- Control of magnetism by external electric field
- Summary





### Control of magnetism of metal thin films by electric field

- **Magnetocrystalline anisotropy (MCA)**  
Weisheit et al., Science 315, 349 (2007)  
Maruyama et al., Nature Nanotech. 4, 349 (2009)  
Duan et al., PRL **101**, 137201 (2008)  
Nakamura et al., PRL **102**, 187201 (2009); PRB **80**, 172402 (2009)  
Tsujikawa et al., PRL **102**, (2009)  
.....
- **Curie temperature ( $T_C$ )**  
Chiba et al., Nat. Mater. 10, 853-856 (2011)  
Oba et al., PRL **114**, 107202 (2015)
- **Dzyaloshinskii-Moriya interaction (DMI)**  
Nawaoka et al., Appl. Phys. Express 8, 063004(2015)  
Nakamura et al., (2015)
- **Magnetic moments**  
Obinata et al., Sci. Rep. 5, 14303 (2015)
- **Magneto-optical conductivity**  
Hibino et al., (2015)  
Nakamura et al., J. Korean Phys. Soc. **63**, 612 (2013)
- **Magnetic dumping**  
Okada et al., Appl. Phys. Lett. 105, 052415 (2014)
- **Magnetic phase-transition (bcc Fe vs fcc Fe)**  
Gerhard et al., Nat. Nanotech., 5, 792 (2010)
- etc.

**Magnetocrystalline anisotropy**

MgO/Fe/Au(001)

Negative Voltage  
Positive Voltage

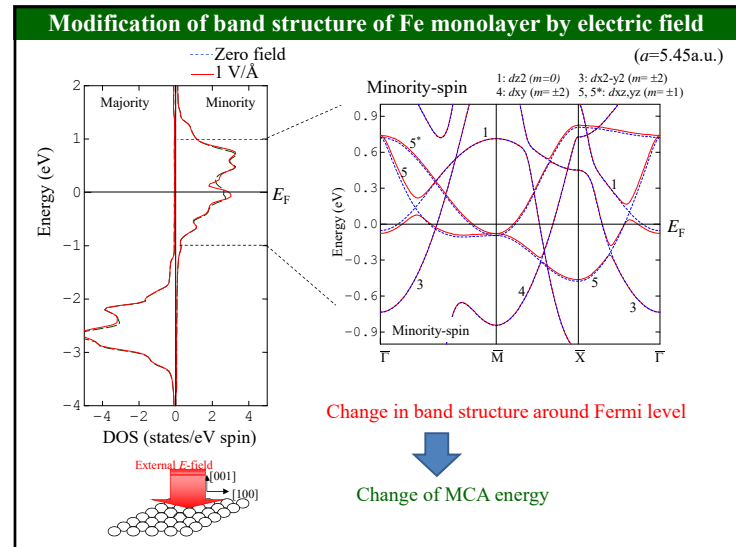
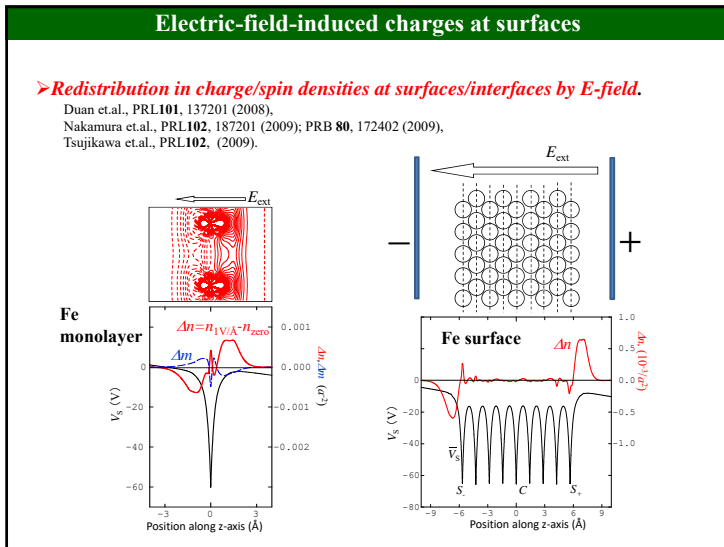
Maruyama et al., Nature Nanotech. 4, 349 (2009)

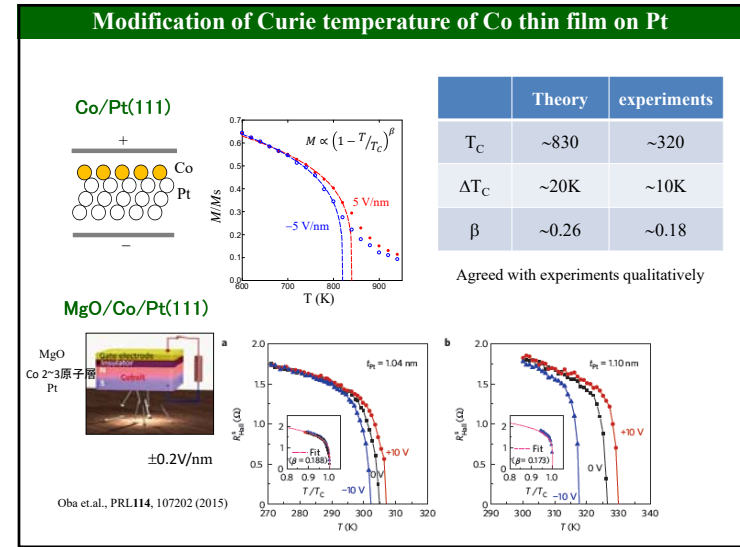
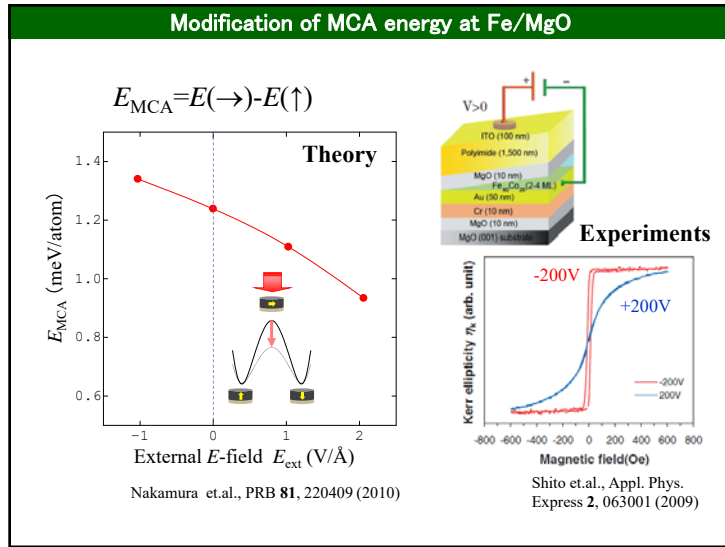
**Curie temperatures**

MgO/Cv/Pt(111)

Positive Voltage  
Negative Voltage

Chiba et al., Nat. Mater. 10, 853-856 (2011)





### Summary

## Spintronic · Design · Magnetic control

**Artificial multilayer thin-films**

Importance of understanding electronic structures

↔

**magnetic properties**

- ✓ Perpendicular magnetization
- ✓ Tunnel magneto resistance
- ✓ Spin current and torque
- ✓ etc.

**Key ideas for PMCA**

- Interface-induced PMCA
- Atomic-layer-alignment-tuned PMA (artificial multilayers)

- Crystal structures and atomic arrangements
- The number of valence electrons
- Eigenvalues and eigenstates of s, p, d, f orbitals
- d-d (d-sp) hybridization